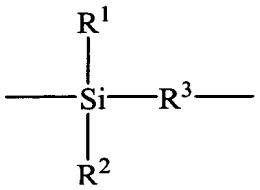
IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): An insulation film comprising an organosilicon polymer with a relative dielectric constant of 4 or less having a dry etching selection ratio to the compound selected from the group consisting of silicon oxide, fluorine-doped silicon oxide, organosilicate glass, carbon-doped silicon oxide, methyl silsesquioxane, hydrogen silsesquioxane, a spin-on-glass, polyorganosiloxane, and an organic polymer selected from the group consisting of polyarylene, polyarylene ether, polyimide, and fluororesin, wherein the organosilicon polymer is at least one polycarbosilane selected from the group consisting of polymers having the structural unit of the following formula (1),



(1)

wherein R^1 and R^2 independently represent a hydrogen atom, an alkyl group having 1-30 carbon atoms that may have a substituent, an alkenyl group having 1-30 carbon atoms that may have a substituent, an alkynyl group having 1-30 carbon atoms that may have a substituent, or an aromatic group that may have a substituent and R^3 represents –C≡C–, $-CH_2-$ or fluoro-substituted $-CH_2-$ having a substituent linked with at least one –C≡C– group, an alkylene or fluoro-substituted alkylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, an alkenylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, an alkynylene group having 2-30 carbon atoms and having a substituent linked with at least one –C≡C– group, or a divalent aromatic group having [[2-30]] 6-30 carbon atoms and having a substituent linked with at least one –C≡C– group.

Claim 2 (Original): The insulation film according to claim 1, wherein the dry etching selection ratio is 1/3 or less.

Claims 3-4 (Canceled).

Claim 5 (Previously Presented): A coating solution composition comprising (I) the organosilicon polymer described in claim 1 and (II) an organic solvent.

Claim 6 (Original): A method of forming an insulating film comprising applying the coating solution composition of claim 5 to a substrate and heating the applied composition.

Claim 7 (Original): A method of forming an insulating film comprising applying the coating solution composition of claim 5 to a substrate and heating the applied composition in the presence of oxygen or peroxide to three-dimensionally crosslink the composition.

Claim 8 (Original): An etching stopper comprising the insulation film described in claim 1 formed below an upper layer film comprising a compound selected from the group consisting of silicon oxide, fluorine-doped silicon oxide, organosilicate glass, carbon-doped silicon oxide, methyl silsesquioxane, hydrogen silsesquioxane, spin-on glass, and polyorganosiloxane or an upper layer film comprising an organic polymer selected from the group consisting of polyarylene, polyarylene ether, polyimide, and fluororesin and having an etch rate of 1/3 or less of the plasma dry etching rate of the upper layer film.

Claim 9 (Original): A hard mask comprising the insulation film described in claim 1 formed on an under layer film comprising a compound selected from the group consisting of silicon oxide, fluorine-doped silicon oxide, organosilicate glass, carbon-doped silicon oxide, methyl silsesquioxane, hydrogen silsesquioxane, spin-on glass, and polyorganosiloxane or an under layer film comprising an organic polymer selected from the group consisting of polyarylene, polyarylene ether, polyimide, and fluororesin and having an etch rate of 1/3 or less of the plasma dry etching rate of the under layer film.

Claim 10 (Previously Presented): A method comprising dry etching an insulation film using the etching stopper of claim 8.

Claim 11 (Previously Presented): A method comprising damascene structure processing using the etching stopper of claim 8.

Claim 12 (Previously Presented): A method comprising dual damascene structure processing using the etching stopper of claim 8.

Claim 13 (Previously Presented): A method comprising dry etching an insulation film using the hard mask of claim 9.

Claim 14 (Previously Presented): A method comprising damascene structure processing using the hard mask of claim 9.

Claim 15 (Previously Presented): A method comprising dual damascene structure processing using the hard mask of claim 9.

DISCUSSION OF THE AMENDMENT

Claim 1 has been amended by changing "2-30" to --6-30--, for the divalent aromatic group member of the R^3 Markush group, as supported in the specification at page 9, lines 8ff (a phenylene group, . . .).

No new matter is believed to have been added by the above amendment. With entry thereof, Claims 1, 2 and 5-15 will remain pending in the application.